

Sub C1
Gnd.
one element selected from the group consisting of rhodium, ruthenium, iridium, osmium, and platinum, and as an adding element at least one element selected from the group consisting of nickel and titanium.

2. (Amended) A semiconductor device equipped with a capacitor for storing information comprising a substrate, a first capacitor electrode formed on the substrate, an oxide film formed in contact with the first capacitor electrode, a second capacitor electrode formed in contact with the oxide film, and an insulating film containing silicon as a main constituting element and formed in contact with the first capacitor electrode and second capacitor electrode, said first capacitor electrode or said second capacitor electrode containing as a main constituting element ruthenium, and as an adding element at least one element selected from the group consisting of nickel and titanium.

Sub B2 Q3
14. (Amended) A process for producing a semiconductor device equipped with a capacitor for storing information comprising a substrate, a first capacitor electrode formed on the substrate, an oxide film for a dielectric formed in contact with the first capacitor electrode, a second capacitor electrode formed in contact with the oxide film, and an insulating film containing silicon as a main constituting element and formed in contact with the first capacitor electrode and second capacitor electrode, which comprises forming at least one of the first capacitor electrode and the second capacitor electrode by using
(a) at least one element selected from the group consisting of rhodium, ruthenium, iridium, osmium and platinum as a main constituting element, or
(b) at least one material selected from the group consisting of ruthenium oxide and iridium oxide as a main constituting material, and at least one element selected from the group consisting of nickel and titanium as an adding element.

16. (Amended) A semiconductor device equipped with a capacitor for storing information comprising:

a first capacitor electrode;

a second capacitor electrode;

an oxide film; and

an insulating film, said insulating film being formed outside of said first capacitor electrode or said second capacitor electrode,

wherein said first capacitor electrode or said second capacitor electrode contain as a main constituting element at least one element selected from the group consisting of rhodium, ruthenium, iridium, osmium, and platinum, and, near the boundary of said insulating film, said first capacitor electrode or said second capacitor electrode includes a region containing an element selected from the group consisting of palladium, nickel, cobalt, and titanium in a concentration of more than about 15 atom %.

Please add new claim 17 as follows:

-- 17. A semiconductor device equipped with a capacitor for storing information comprising a substrate, a first capacitor electrode formed on the substrate, an oxide film formed in contact with the first capacitor electrode, a second capacitor electrode formed in contact with the oxide film, and an insulating film containing silicon as a main constituting element and formed in contact with the first capacitor electrode and second capacitor electrode, said first capacitor electrode or said second capacitor electrode containing as a main constituting element at least one element selected from the group consisting of rhodium, ruthenium, iridium, osmium, and platinum, and means for enhancing adhesiveness of said first or said second capacitor electrode to said insulating film to prevent peeling comprising